METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

A technique includes: forming a film of a predetermined substance containing a first element by performing a cycle a predetermined number of times, the cycle including: (a1) supplying, under a predetermined condition, a first gas to a substrate, which includes a recess on a surface, to deposit a first substance containing the first element on the surface, wherein the predetermined condition satisfies: a temperature condition that a substrate temperature is equal to or higher than a decomposition temperature of the first gas, and a first condition that an amount of the first substance adsorbed on an opening portion of the recess increases during a first period after starting supplying the first gas, the amount gradually approaches a predetermined value during a second period after the first period, and the amount increases during a third period after the second period, and wherein (a1) is ended during the second period.

FIGs. 5A and 5B